

FIG.2C

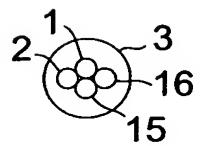
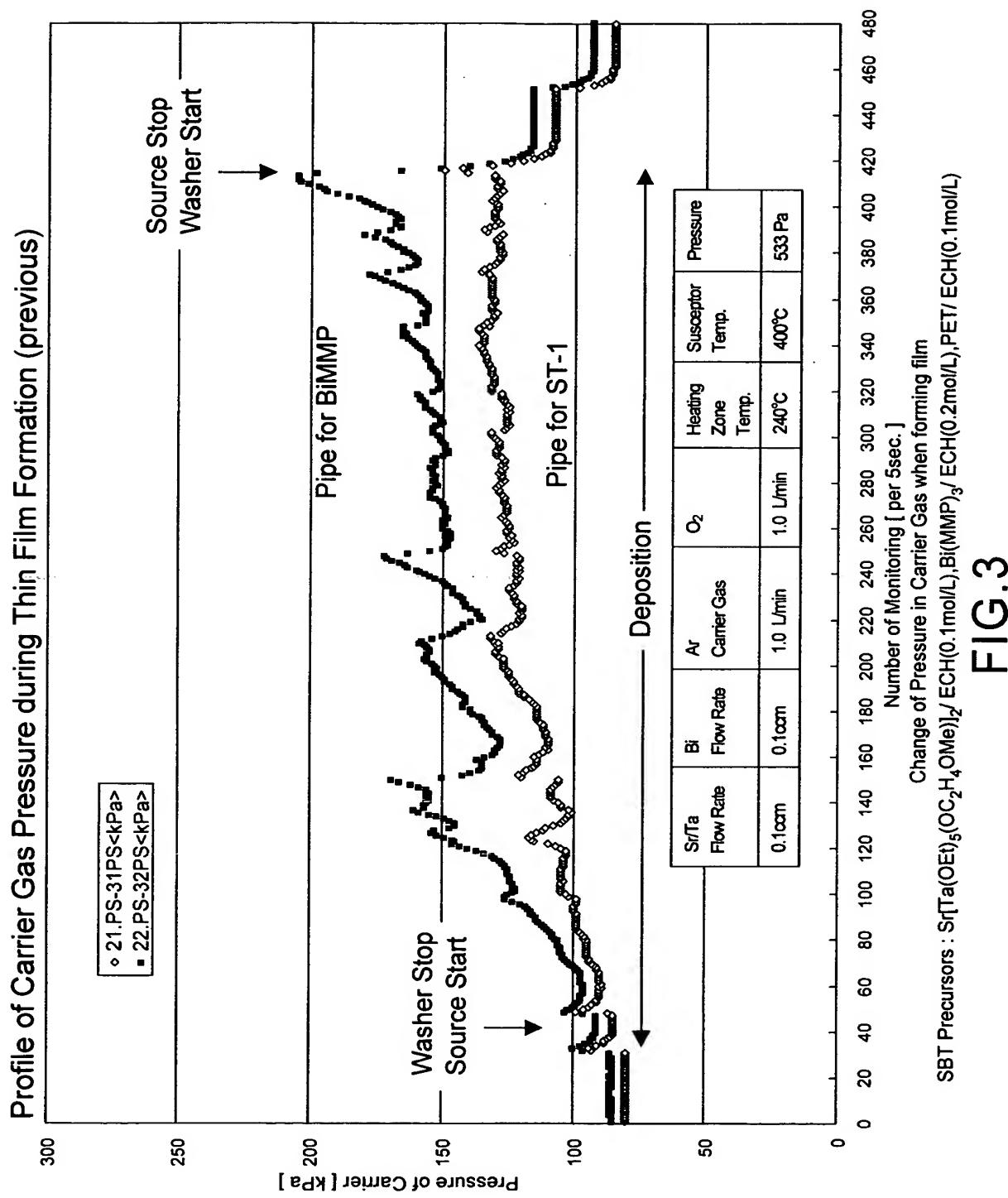
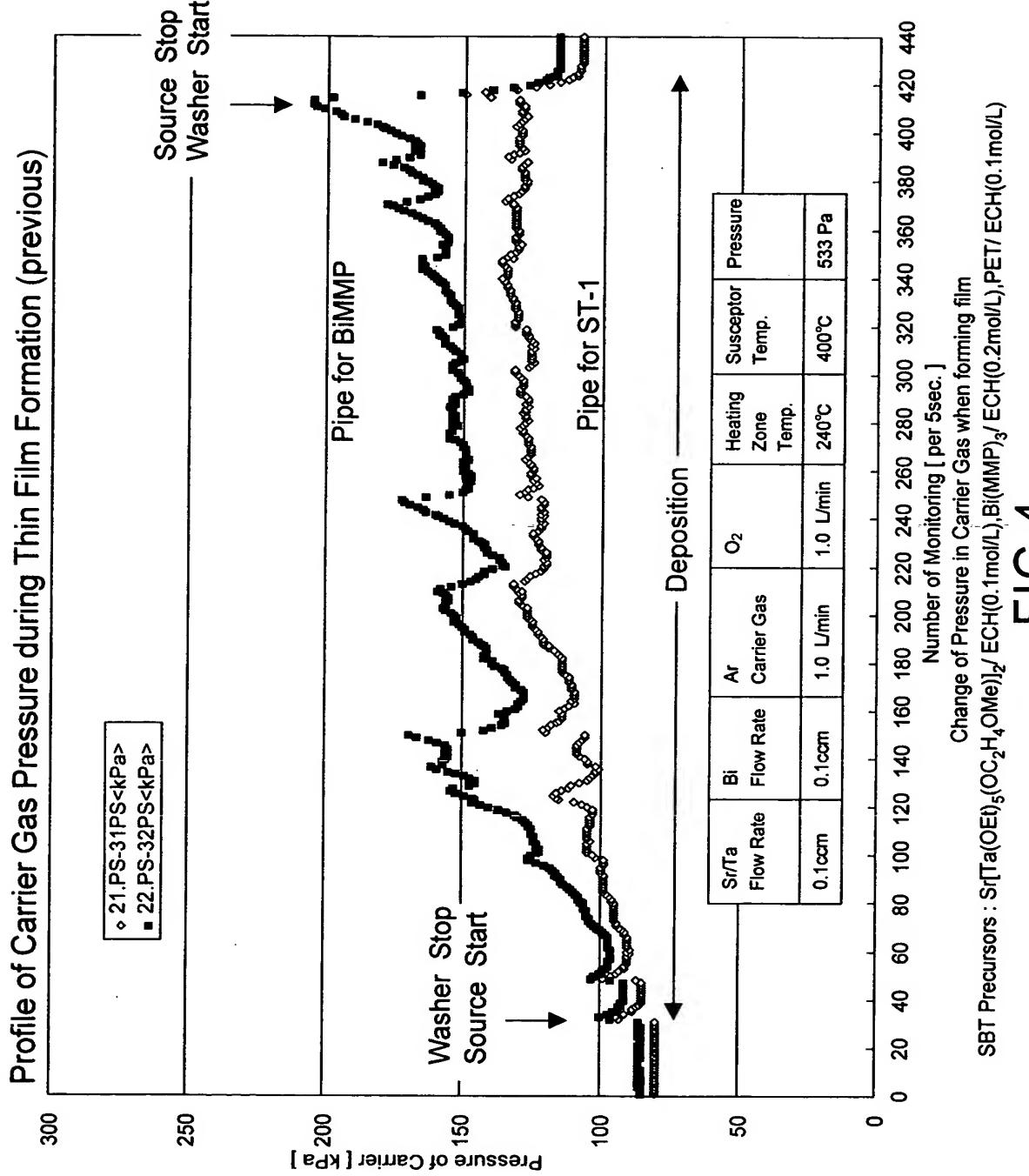
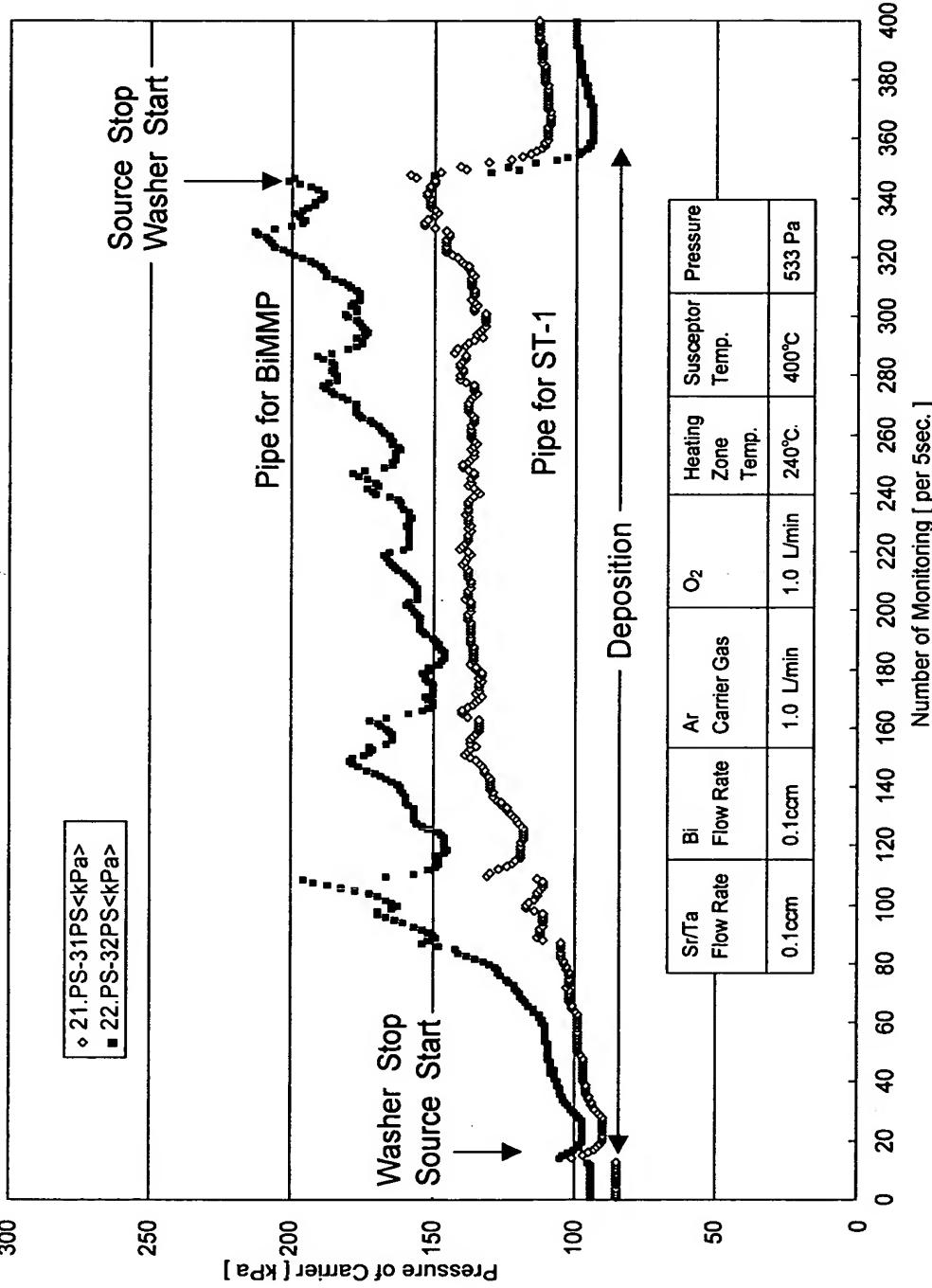


FIG.2D





Profile of Carrier Gas Pressure during Thin Film Formation (previous)



Change of Pressure in Carrier Gas when forming film
 SBT Precursors : Sr[Ta(OEt)₅(OC₂H₄OMe)]₂/ECH(0.1mol/L), Bi(MMP)₃/ECH(0.2mol/L), PET/ECH(0.1mol/L)

FIG. 5

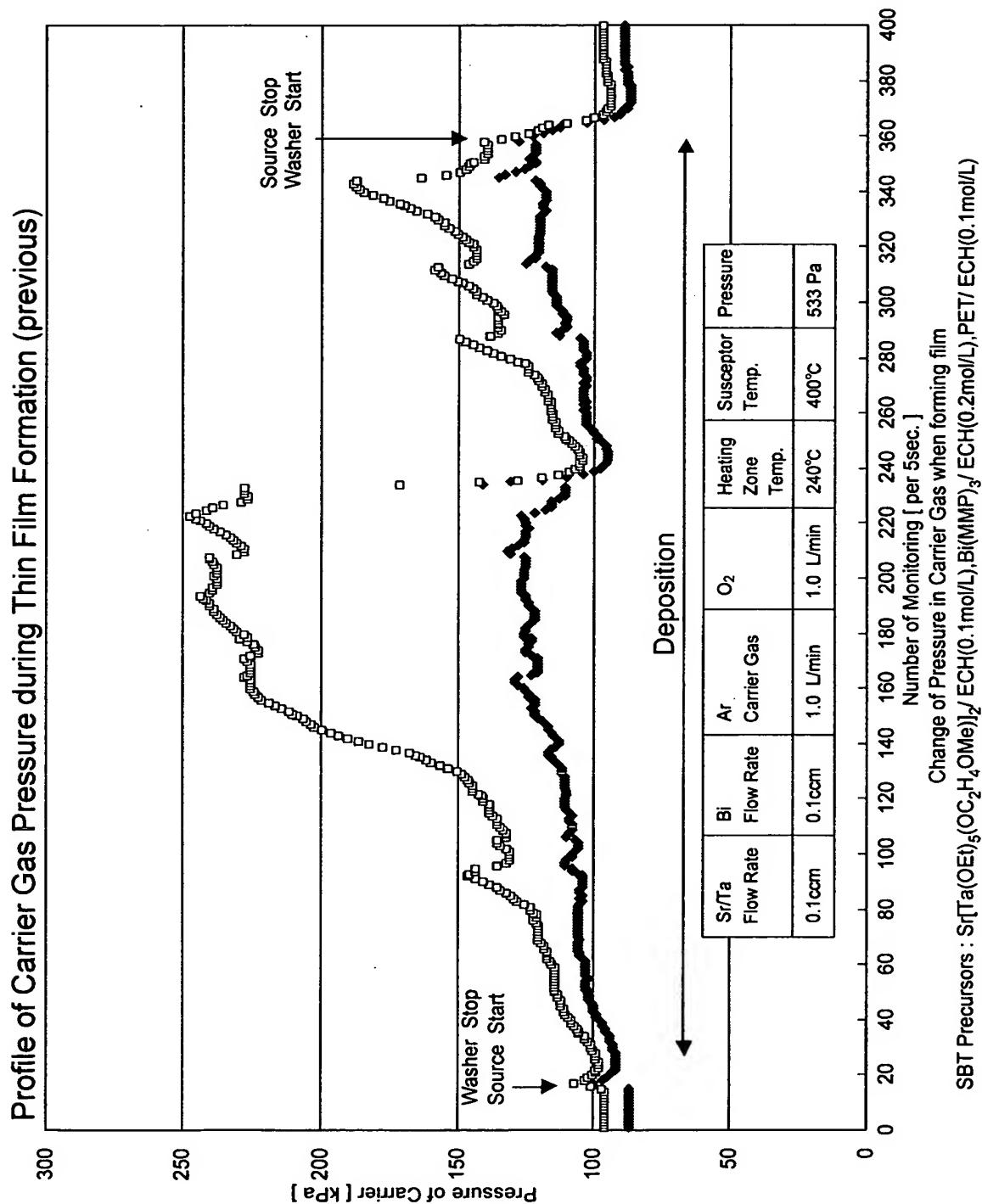


FIG. 6

Profile of Carrier Gas Pressure during Thin Film Formation (previous)

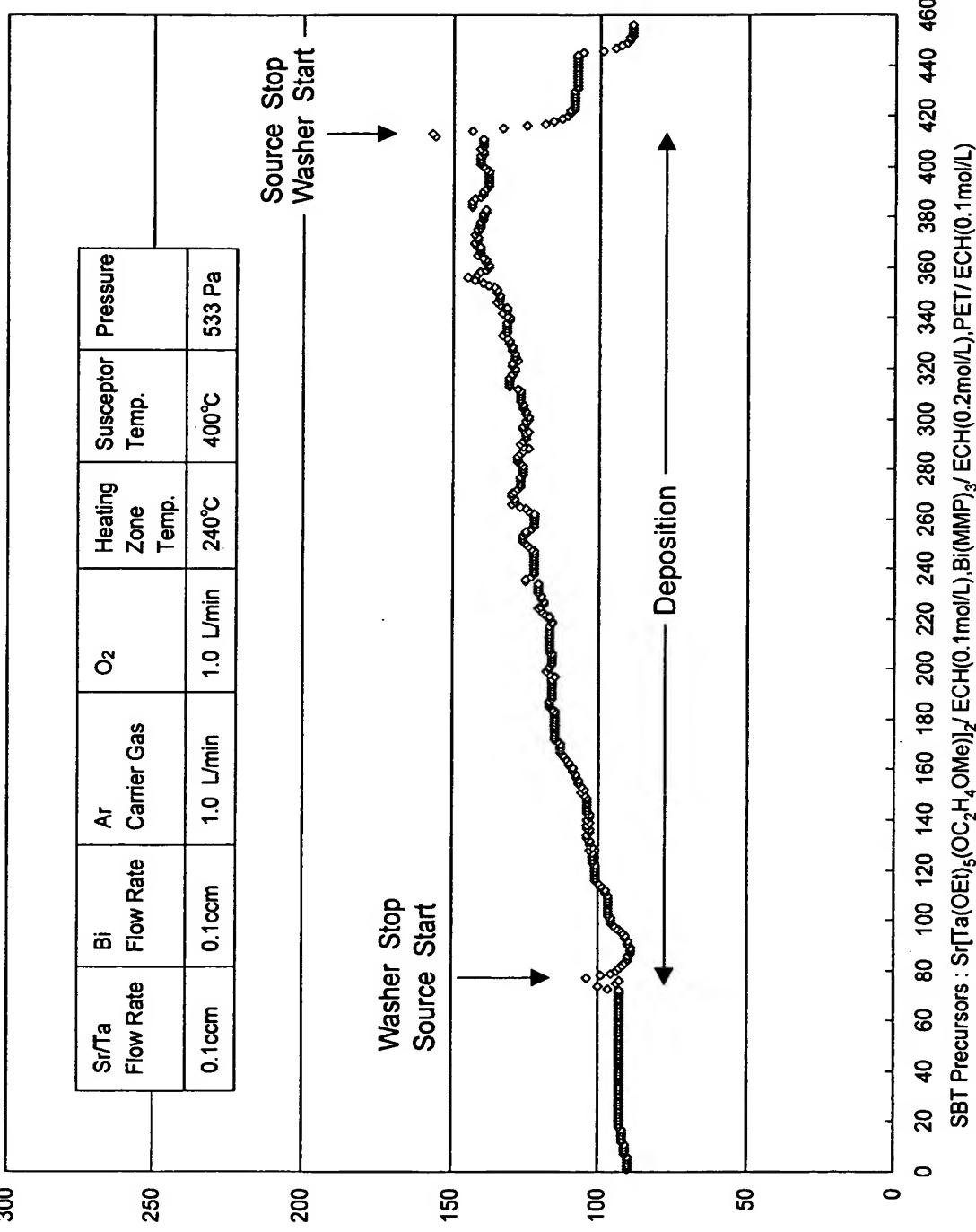
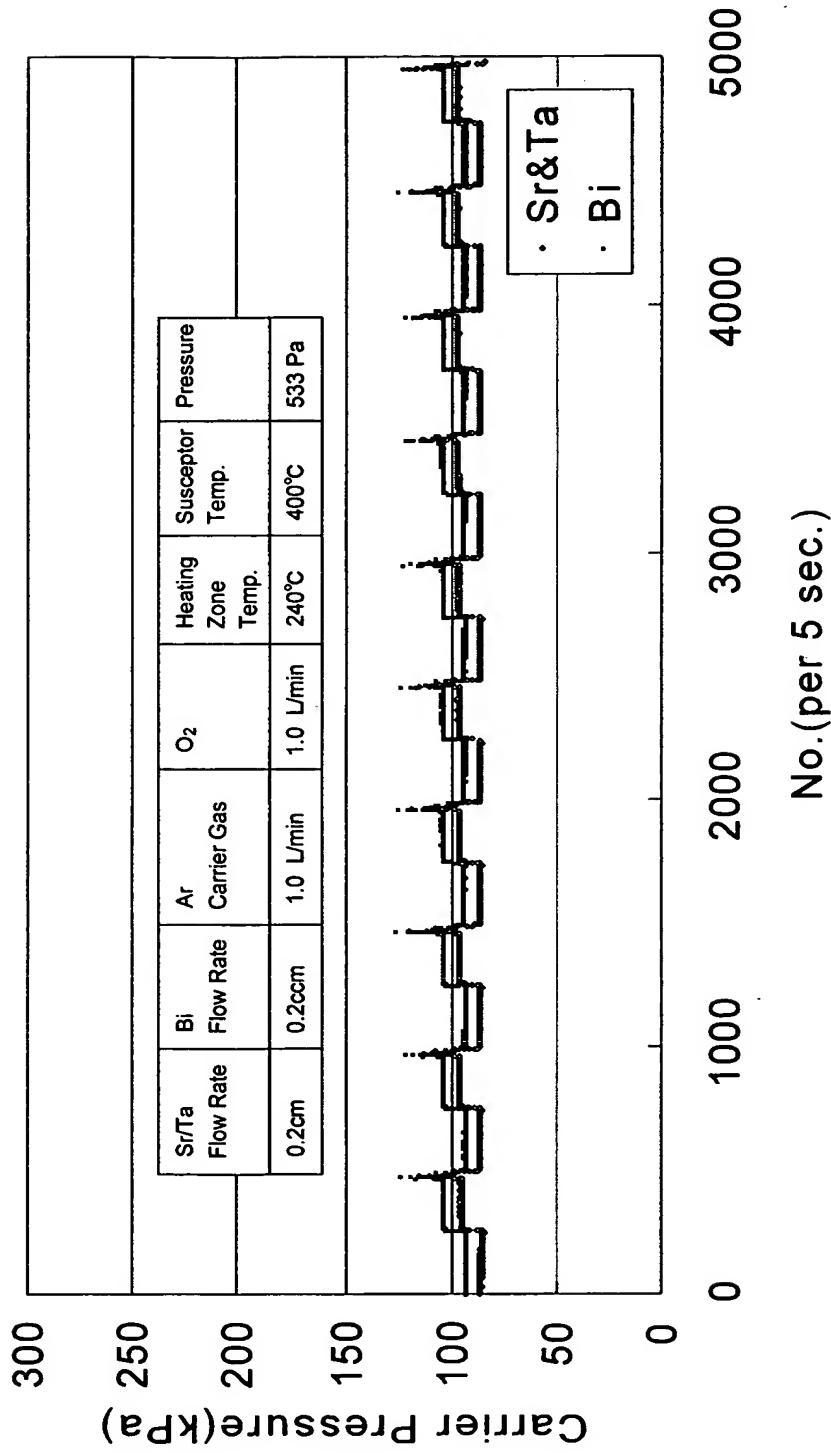


FIG. 7

Profile of Carrier Gas Pressure during Thin Film Formation (Current)



SBT Precursors : Sr[Ta(OEt)₅(OC₂H₄OMe)]₂ / ECH(0.05mol/L), Bi(MMP)₃ / ECH(0.1mol/L), PET / ECH(0.05mol/L)

FIG. 8

Continuous Running Test Result (SBT Depo. Rate, Si Wafer)

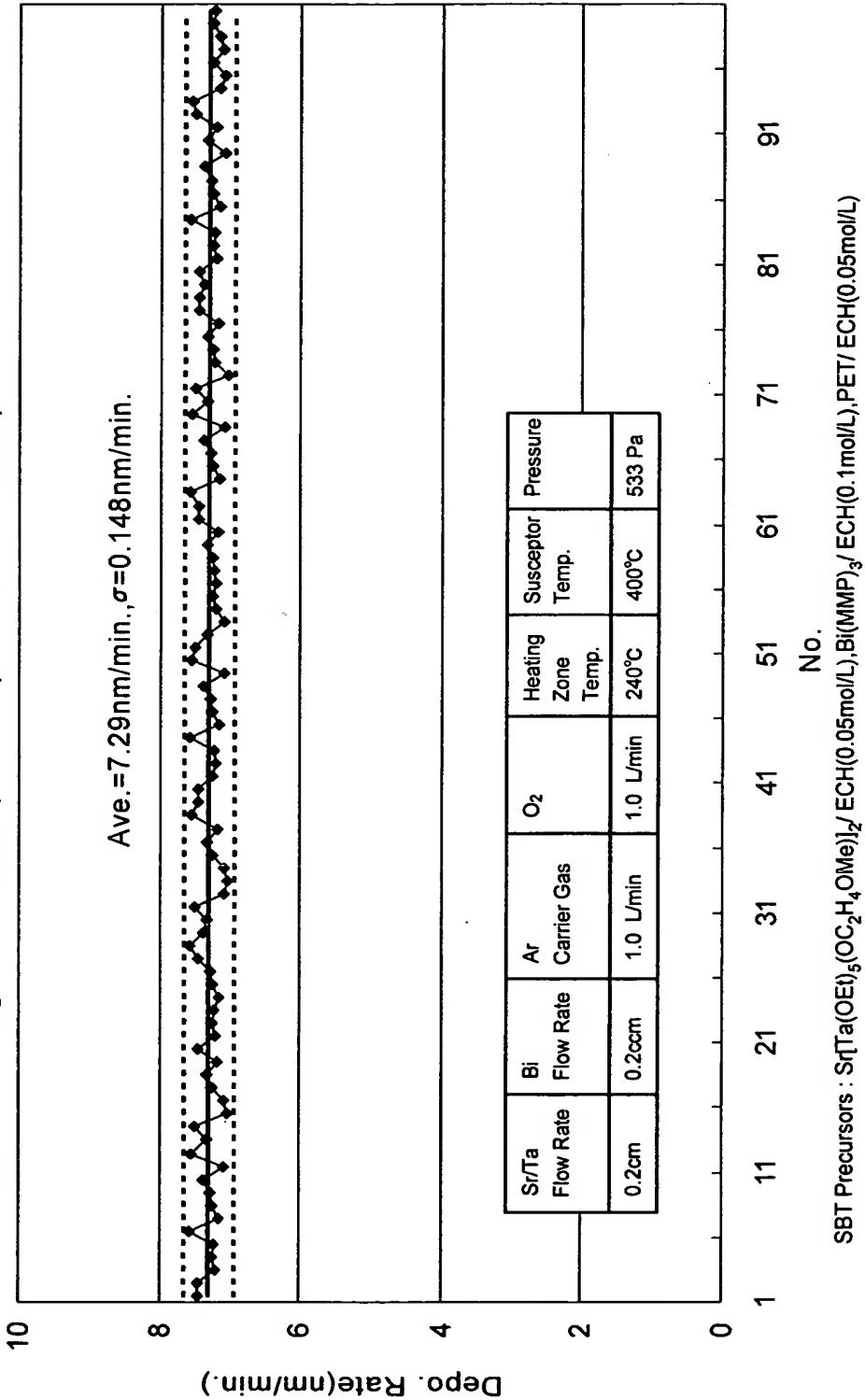


FIG.9

Continuous Running Test Result (SBT Composition, Si Wafer)

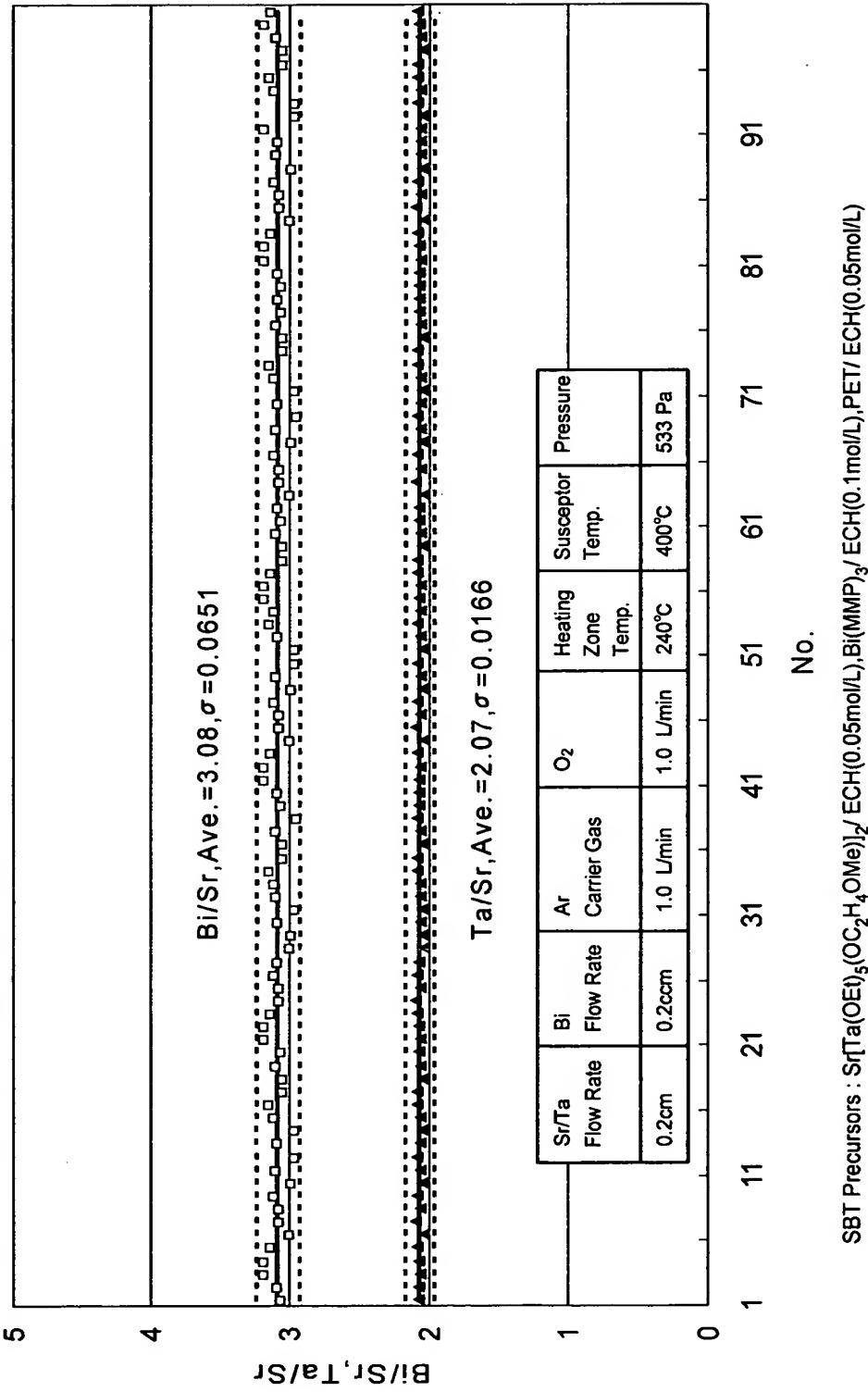


FIG.10

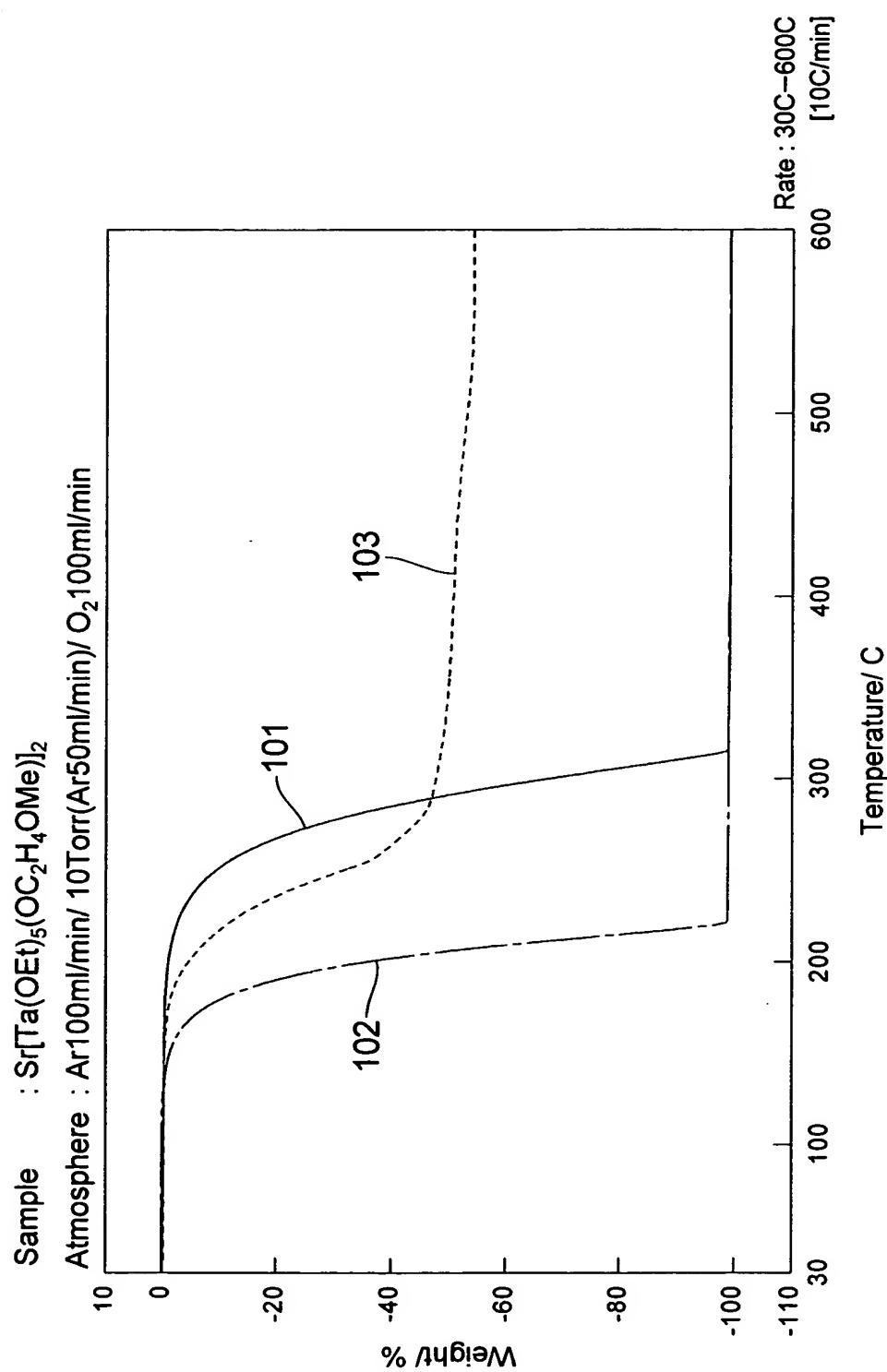


FIG.11

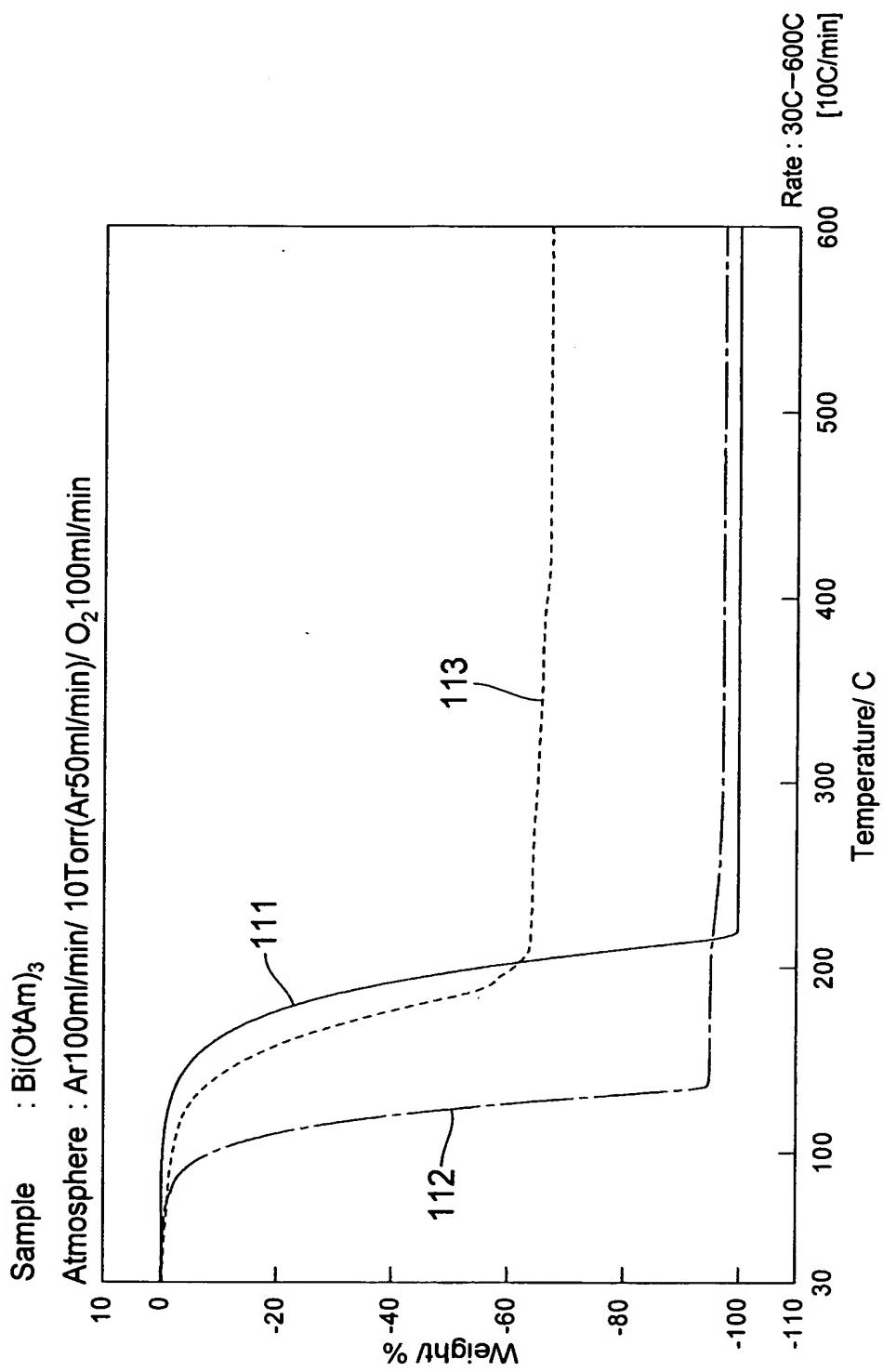


FIG.12

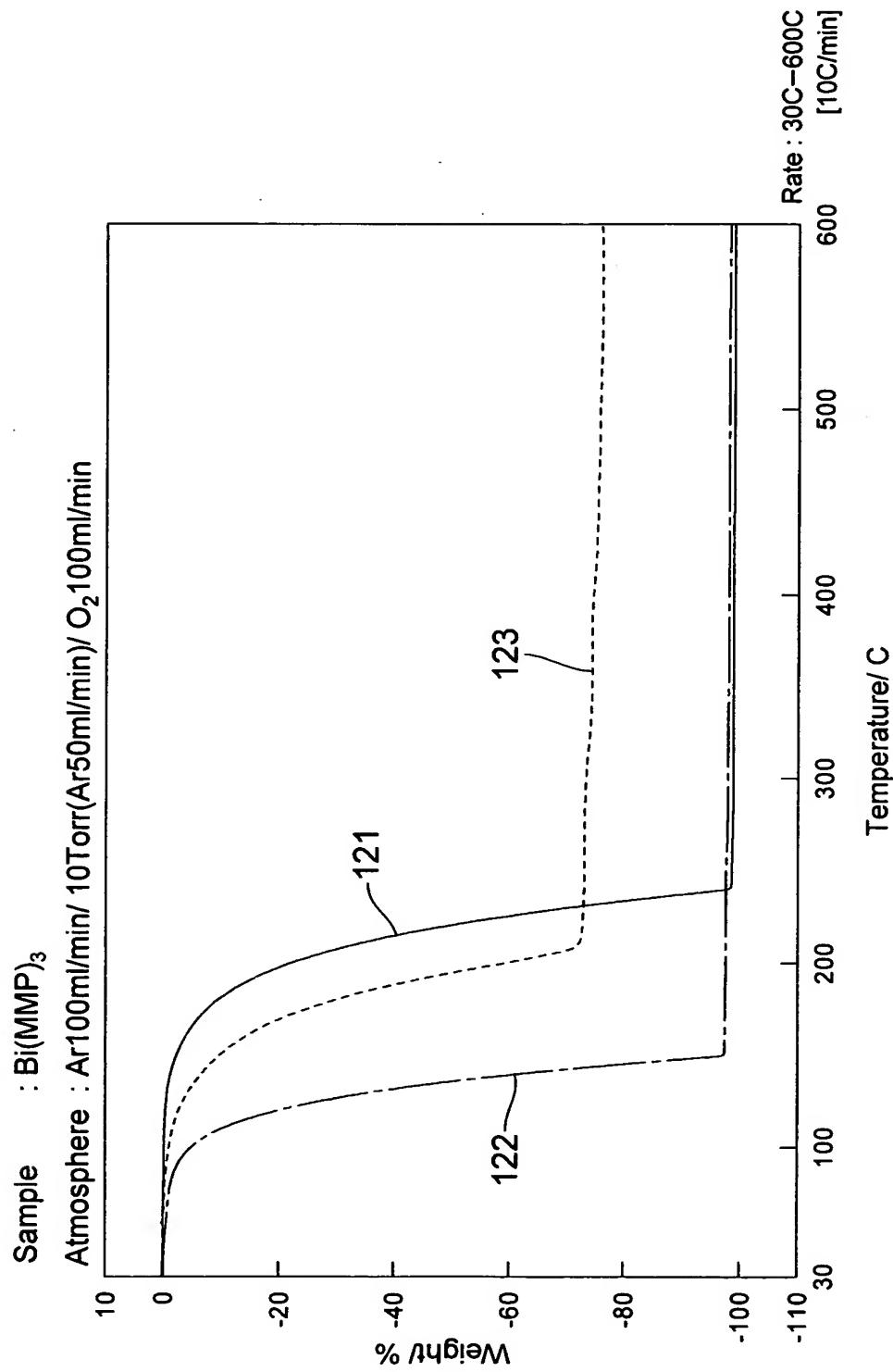


FIG. 13

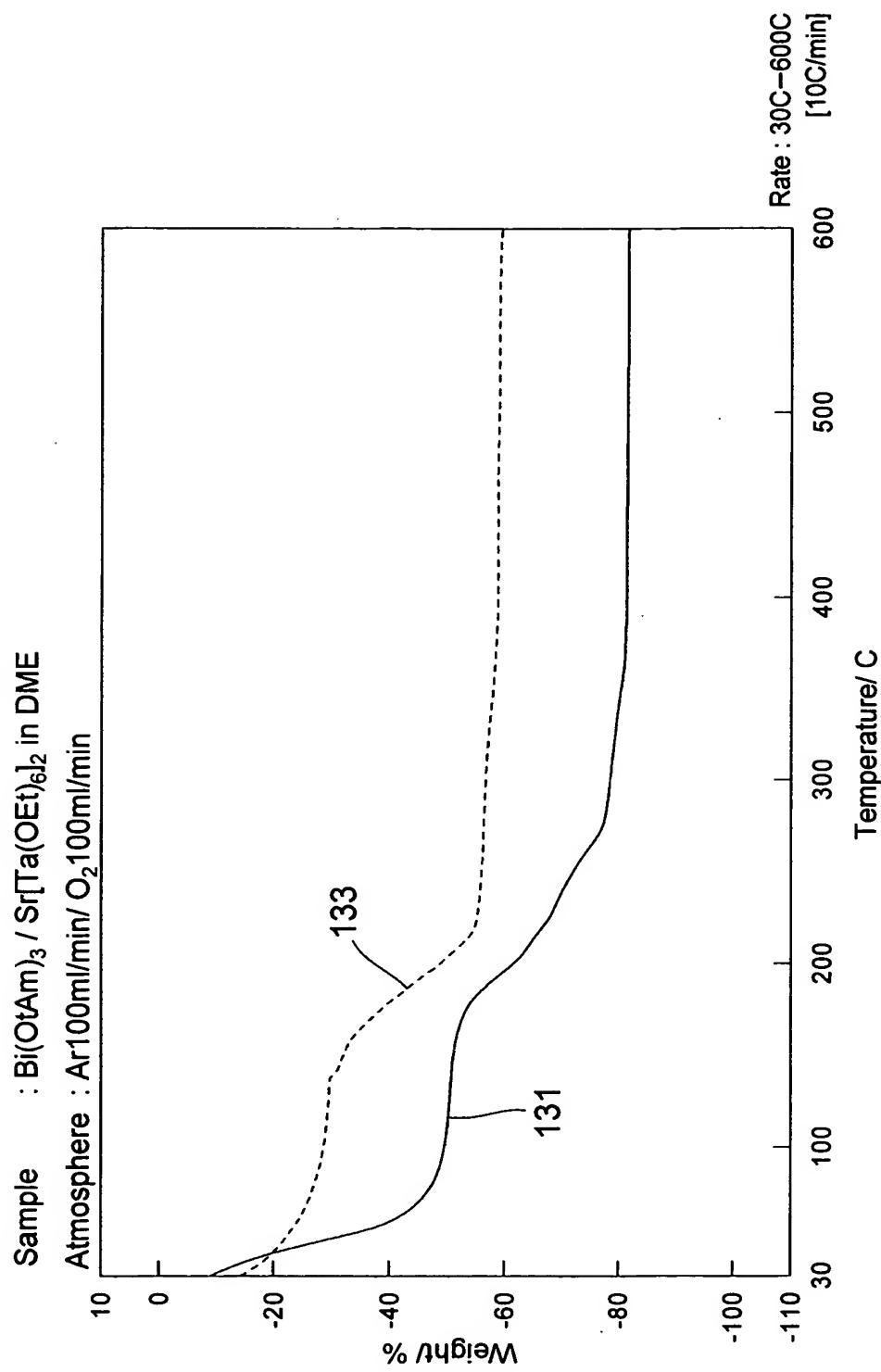


FIG.14

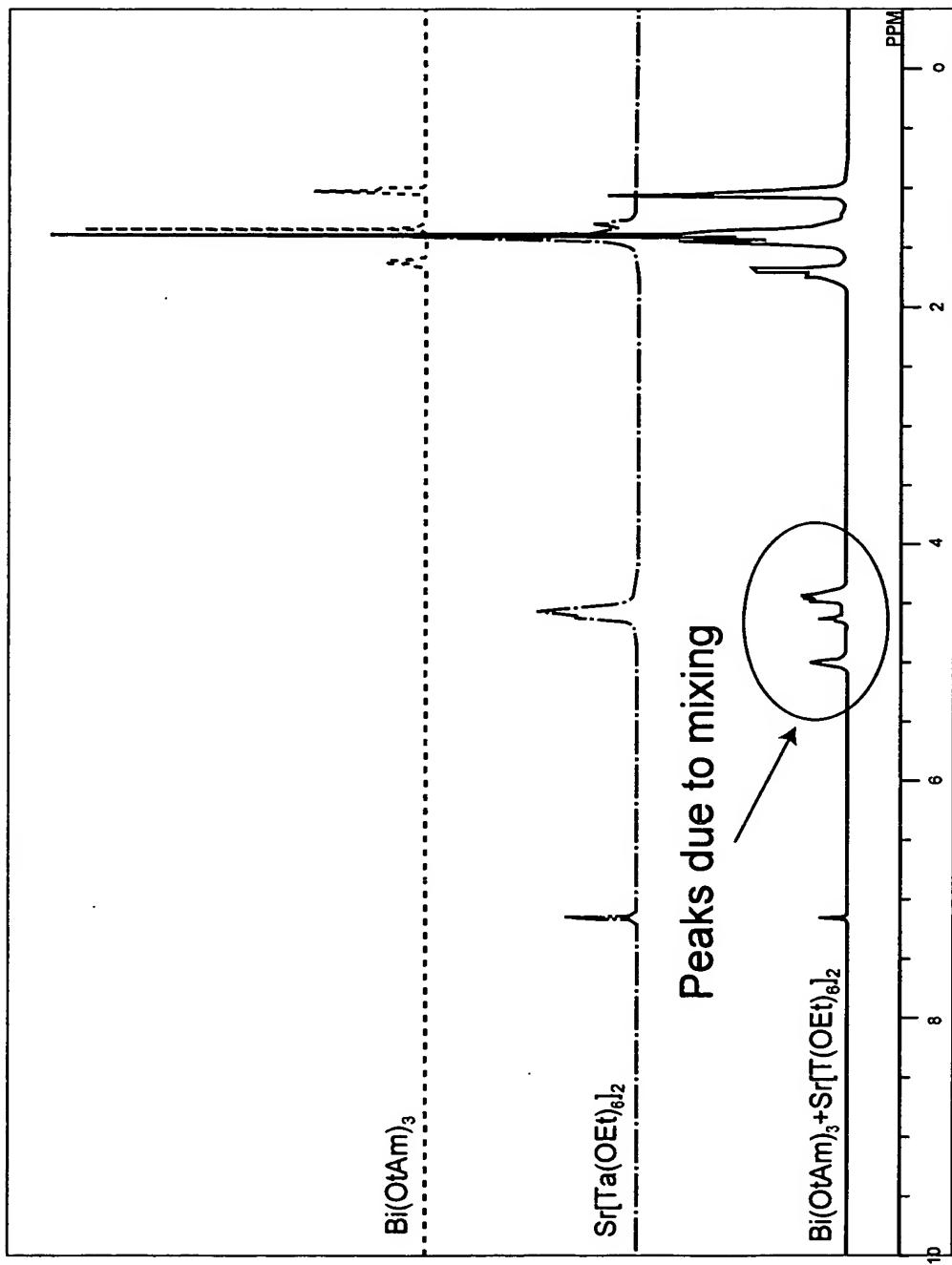


FIG.15

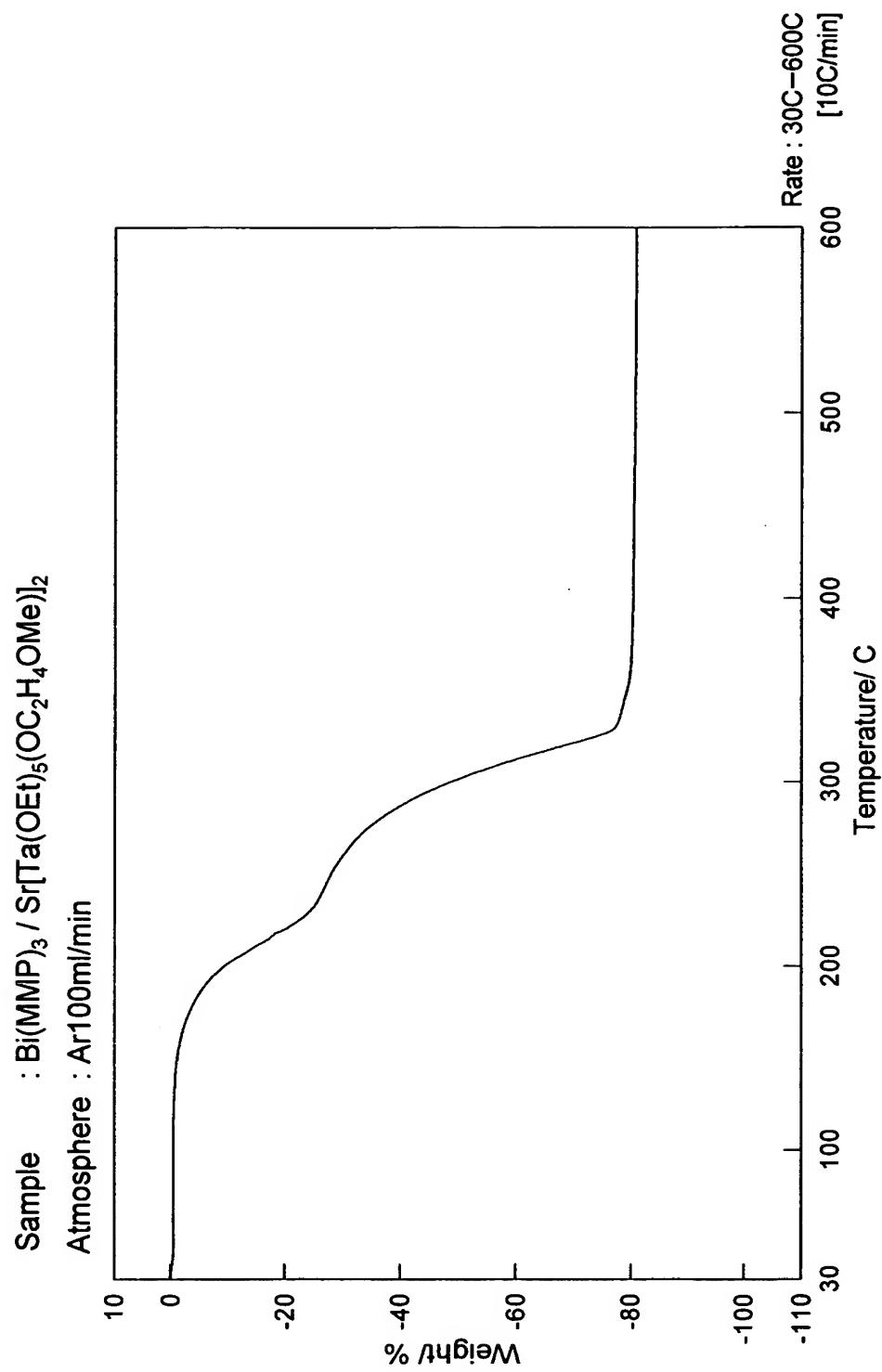


FIG.16

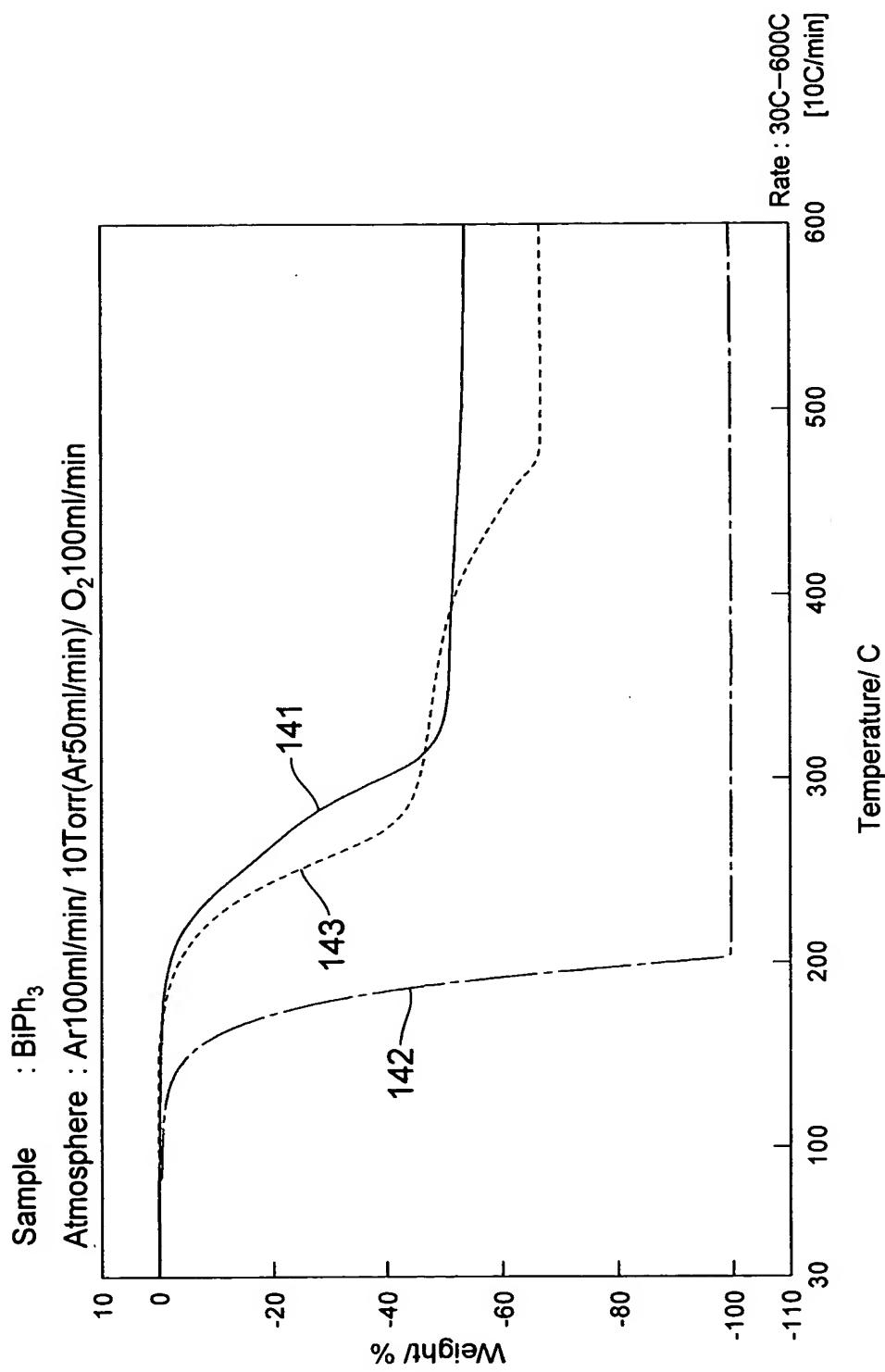


FIG. 17

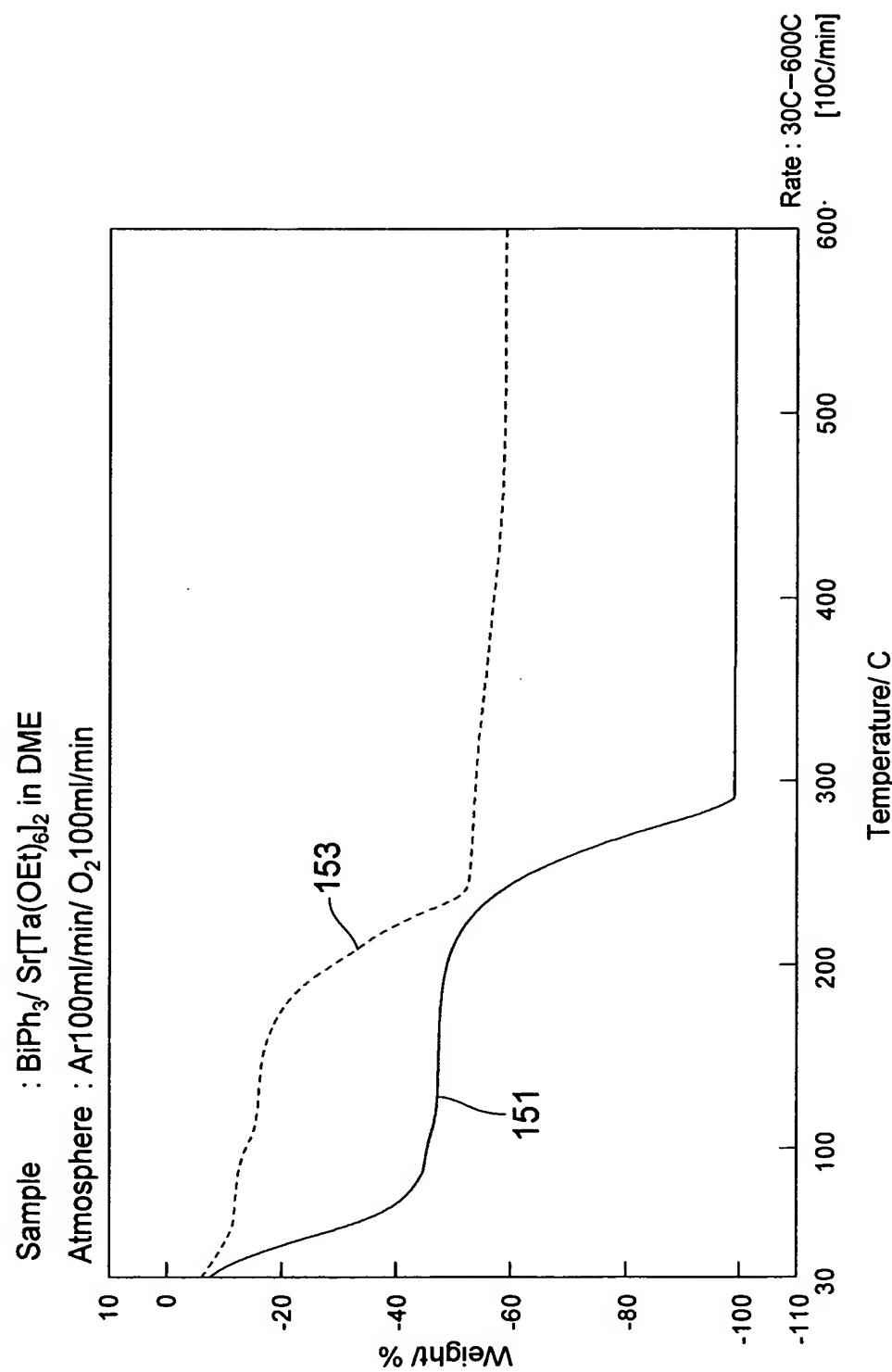


FIG. 18

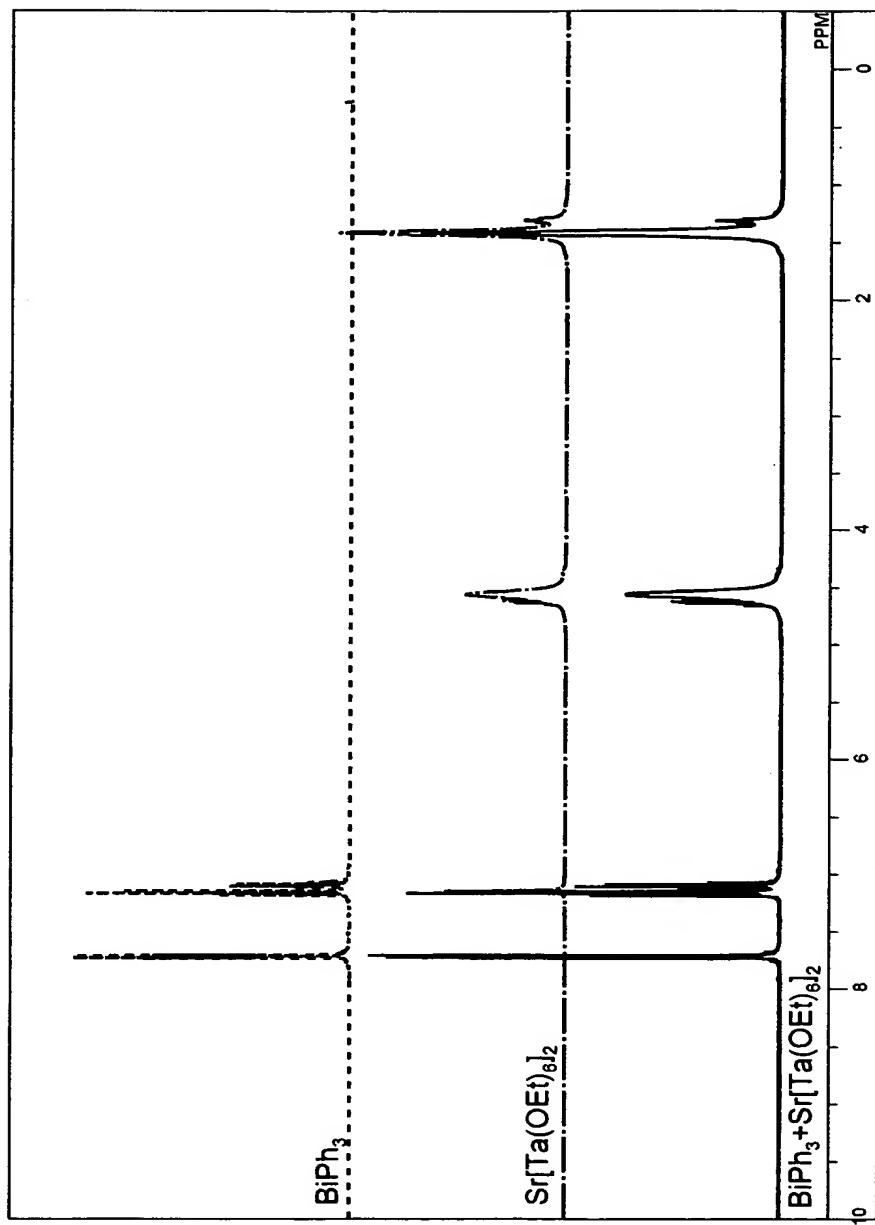


FIG.19

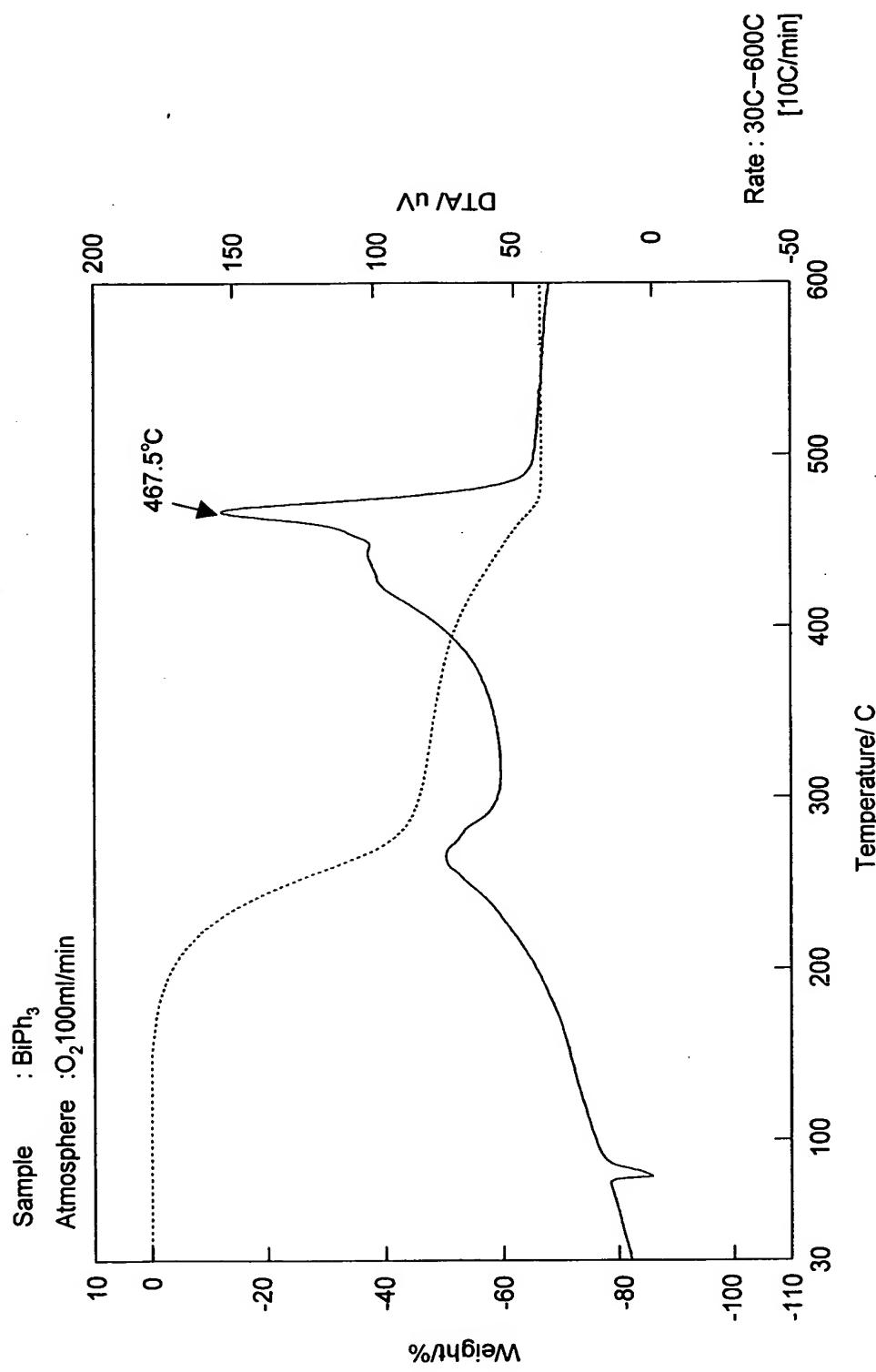


FIG.20